

What is claimed is:

1     A semiconductor light emitting device,  
comprising:

5     a semiconductor layered portion having a light  
emitting layer forming portion;

a conductive substrate; and

a metal layer for adhering said semiconductor  
layered portion to said conductive substrate,

10     wherein said metal layer includes at least a  
first metal layer for making ohmic contact with said  
semiconductor layered portion, a second metal layer  
essentially consisted of Ag, and a third metal layer  
made of a metal which allows to adhere to said  
conductive substrate and said semiconductor layered  
15     portion at a low temperature.

2     The semiconductor light emitting device  
according to claim 1, wherein said first metal layer is  
partially removed so as to form a missing portion.

3     The semiconductor light emitting device  
20     according to claim 2, wherein said missing portion  
occupies 50% or less of a surface area of said  
semiconductor layered portion.

4     The semiconductor light emitting device  
according to claim 2, wherein a protective film is  
25     provided in said missing portion, said protection film  
being a film for preventing the Ag in said second metal  
layer from diffusing into said semiconductor layered

portion, and for transmitting light emitted in said light emitting layer forming portion.

5        5     The semiconductor light emitting device according to claim 4, wherein said protective film is made of  $\text{SiO}_2$  or  $\text{Al}_2\text{O}_3$ .

6        6     The semiconductor light emitting device according to claim 1, wherein Ag is added to said first metal layer.

7        7     The semiconductor light emitting device  
10     according to claim 1, wherein said second metal layer contains at least either Zn or Au at 10 atomic % or less, and comprises Ag at 90 atomic % or greater.

8        8     The semiconductor light emitting device  
15     according to claim 1, wherein said second metal layer is formed to have a thickness of from 0.1 to 0.5  $\mu\text{m}$ .

9        9     The semiconductor light emitting device according to claim 1, wherein said third metal layer comprises at least one selected from a group of In, In-Zn alloy, and Sn-Zn alloy.

10       10     The semiconductor light emitting device  
20     according to claim 1, wherein said conductive substrate is formed of a semiconductor substrate, and a fourth metal layer for making an ohmic contact with said semiconductor substrate is provided on a side of said  
25     metal layer, said side being contact with said semiconductor substrate.

11       11     The semiconductor light emitting device

according to claim 10, wherein said fourth metal layer is made of at least one selected from a group of an Au-Zn alloy, an Au-Be alloy, and an Au-Ge alloy.